

TOSHIBA INFRARED LED GaAs INFRARED EMITTER

TLN108

INFRARED LED FOR PHOTO SENSOR

Unit in mm

OPTO-ELECTRONIC SWITCH

TAPE, CARD READERS

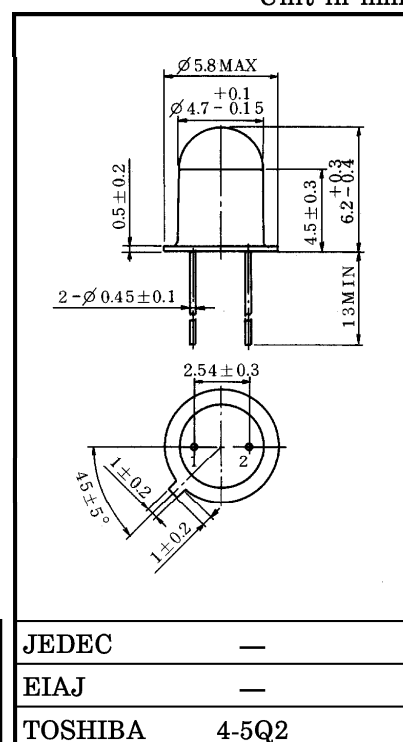
SMOKE SENSOR

INFRARED RAYS APPLIED EQUIPMENT

- TO-18 metal package.
- High radiant intensity : $I_E = 20\text{mW / sr}$ (TYP.)
- Excellent linearity of radiant intensity and modulation by pulse operation and high frequency is possible.
- Highly reliable because of hermetic seal.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Forward Current	I_F	100	mA
Forward Current Derating ($T_a > 25^\circ\text{C}$)	$\Delta I_F / ^\circ\text{C}$	-1	mA / $^\circ\text{C}$
Pulse Forward Current (Note)	I_{FP}	1	A
Reverse Voltage	V_R	5	V
Operating Temperature Range	T_{opr}	$-40 \sim 125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

(Note) Pulse Width $\leq 100\mu\text{s}$, Repetitive Frequency = 100Hz

JEDEC	—
EIAJ	—
TOSHIBA	4-5Q2

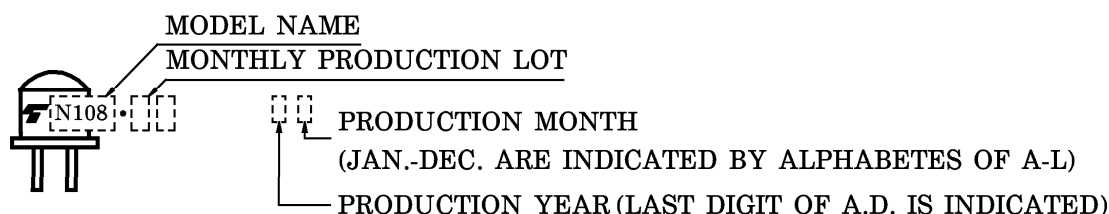
Weight : 0.33g (TYP.)

PIN CONNECTION



1. ANODE
2. CATHODE (CASE)

PRODUCT INDICATION



STAMP COLOR : RED

961001EAC2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

OPTO-ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F = 50\text{mA}$	—	1.3	1.4	V
Pulse Forward Voltage	V_{FP}	$I_{FP} = 1\text{A}$	—	2.4	—	V
Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
Radiant Intensity	I_E	$I_F = 50\text{mA}$	10	20	—	mW / sr
Radiant Power	P_O	$I_F = 50\text{mA}$	—	3	—	mW
Capacitance	C_T	$V_R = 0, f = 1\text{MHz}$	—	30	—	pF
Peak Emission Wavelength	λ_P	$I_F = 50\text{mA}$	—	940	—	nm
Spectral Line Half Width	$\Delta\lambda$	$I_F = 50\text{mA}$	—	50	—	nm
Half Value Angle	$\theta_{\frac{1}{2}}$	$I_F = 50\text{mA}$	—	± 8	—	°

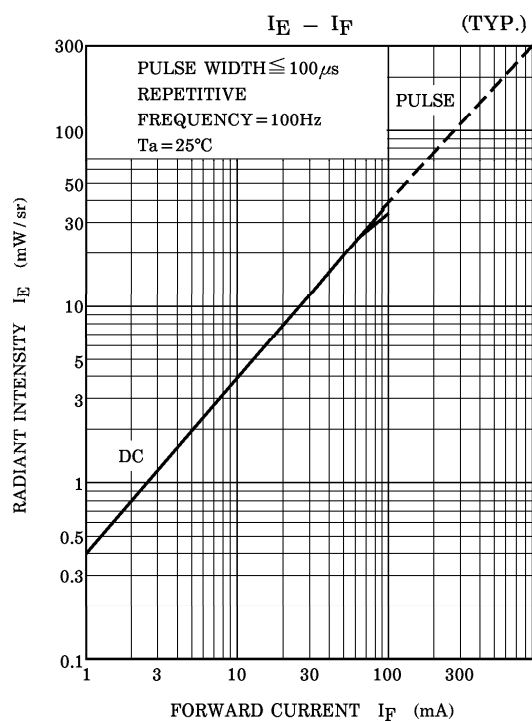
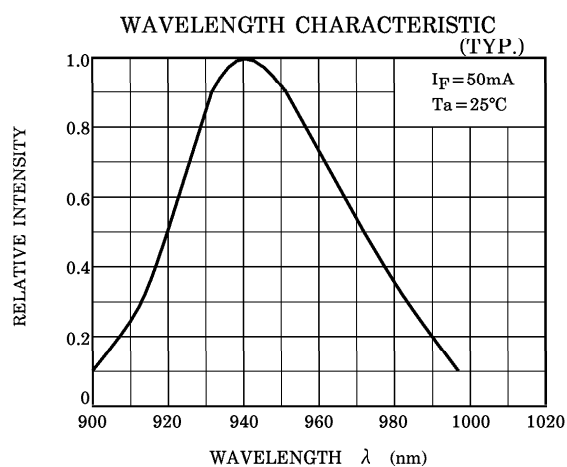
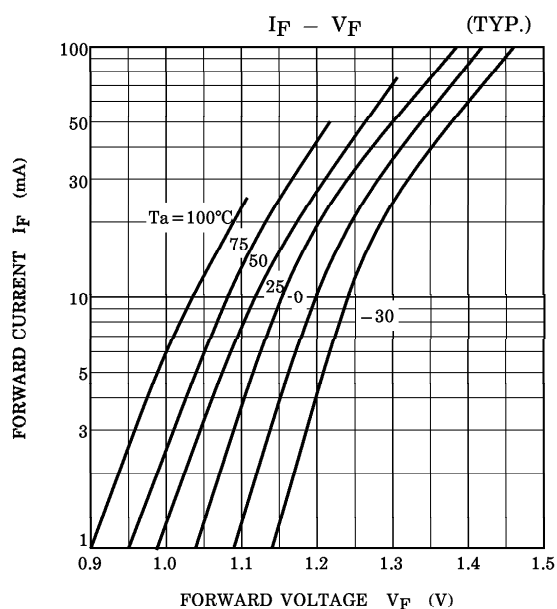
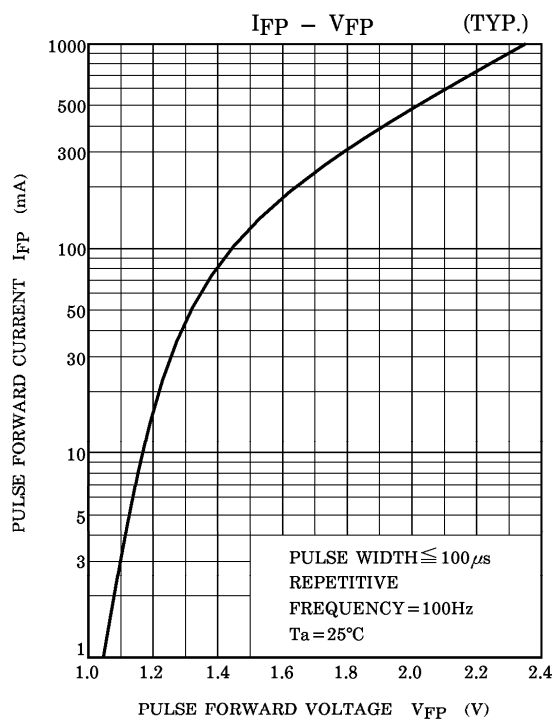
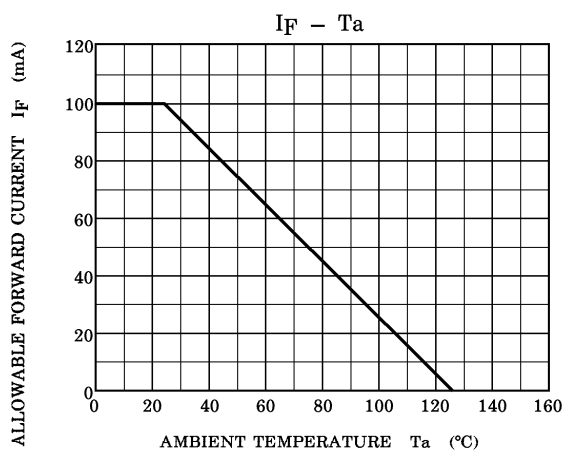
PRECAUTION

Please be careful of the followings.

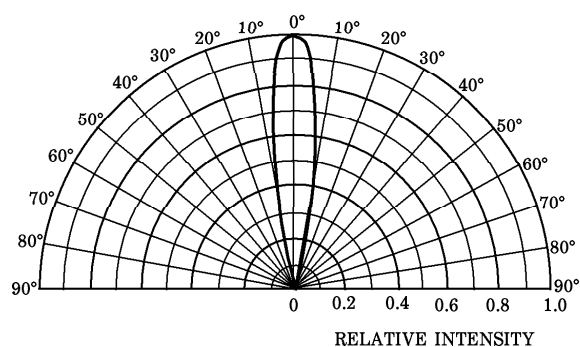
1. Soldering temperature : 260°C MAX.
Soldering time : 5s MAX.
(Soldering portion of lead : above 1.5mm from the body of the device)
2. If the lead is formed, the lead should be formed at a distance of 2mm from the body of the device.
Soldering shall be performed after lead forming.

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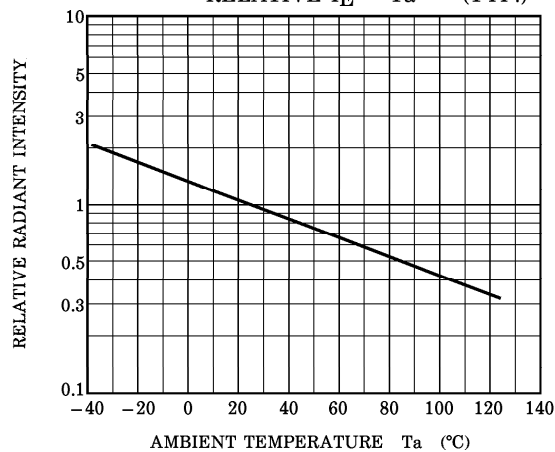
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
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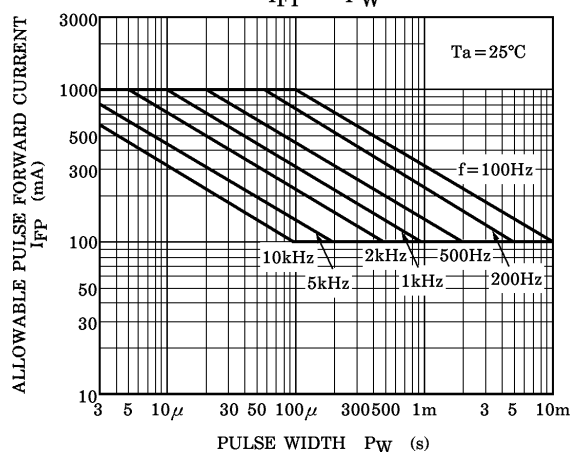
RADIATION PATTERN (TYP.)
($T_a = 25^\circ\text{C}$)



RELATIVE $I_E - T_a$ (TYP.)



$I_{FP} - P_W$



COUPLING CHARACTERISTICS WITH
TPS601A

